



# **Development of SiC MOSFET Electrical Model and Experimental Validation: Improvement and Reduction of Parameter Number**

Nguyen Quang, Patrick Tounsi, Jean-Pierre Fradin, Jean-Michel Reynes

## **► To cite this version:**

Nguyen Quang, Patrick Tounsi, Jean-Pierre Fradin, Jean-Michel Reynes. Development of SiC MOSFET Electrical Model and Experimental Validation: Improvement and Reduction of Parameter Number. 26th International Conference "Mixed Design of Integrated Circuits and Systems" (MIXDES 2019), Jun 2019, Rzeszów, Poland. pp.298 - 301, <10.23919/MIXDES.2019.8787050>. <hal-02613777>

**HAL Id: hal-02613777**

**<https://laas.hal.science/hal-02613777v1>**

Submitted on 9 Jan 2024

**HAL** is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.



HAL Authorization

# Development of SiC MOSFET Electrical Model and Experimental Validation: Improvement and Reduction of Parameter Number

Quang Chuc Nguyen<sup>1,2,3</sup>, Patrick Tounsi<sup>2</sup>, Jean-Pierre Fradin<sup>3</sup>, Jean-Michel Reynes<sup>1,4</sup>

<sup>1</sup>IRT Saint-Exupéry, Toulouse, France

<sup>2</sup>LAAS-CNRS, Toulouse, France

<sup>3</sup>ICAM Toulouse, , Toulouse, France

<sup>4</sup>aPSI<sup>3D</sup>, Toulouse, France

quang-chuc.nguyen@irt-saintexpery.com, patrick.tounsi@laas.fr , jean-pierre.fradin@icam.fr,  
jean-michel.reynes@irt-saintexpery.com

**Abstract**—In this work, a new approach for electrical modeling of Silicon Carbide (SiC) MOSFET is presented. The developed model is inspired from the Curtice model which is using a mathematic function reflecting MOSFET output characteristics. The first simulation results showed good agreement with measurements. Improvement is needed in order to increase model accuracy and to take into account the influence of the junction temperature on device characteristics.

**Keywords**—SPICE model; Silicon Carbide (SiC); MOSFET

## I. INTRODUCTION

In power electronics field, engineers must simulate electrical circuit before building an electrical system. During this phase, a good electrical model of transistors is mandatory because it gives the necessary indications on the behaviors of the systems under different conditions. That is why having a good transistor model is critical. Often, a complex model provides a better accuracy, but it has a longer simulation time. Conversely, a simple model has much shorter simulation time, but often with a mediocre accuracy. Electrical engineers always have to compromise these two aspects.

In most applications, Silicon (Si) power devices play a dominant role because technologies are mature. However, foreseeing their limits [1], a lot of efforts were put in order to find alternative devices. Wide band gap materials such as Silicon Carbide (SiC) and Gallium Nitride (GaN) are two most promising materials to replace Silicon in power devices. Presently, SiC power devices are targeted for replacing Si power devices in high voltage applications. SiC MOSFETs and SiC Schottky diodes are already successfully commercialized and replaced their Si counterparts in some applications with higher overall performances [2], [3]. Electrical models of these devices are necessary for engineers to contemplate which solutions to choose while considering all aspects: performance, price, harsh conditions ... A great amount of works are put into accurately modeling these devices, particularly SiC MOSFET.

In the literature, many models of SiC MOSFET have been proposed [4]. McNutt *et al.* [5] have efficiently adapted a physical model of Si IGBTs for SiC MOSFETs. While the advantage of this model is presenting the MOSFET with physical meaning, it is still limited because of its complexity and its accuracy.

On the industrial side, SiC MOSFET manufacturers also provide electrical models for their own power devices. Some of them (STM, ROHM and CREE Wolfspeed devices) are analyzed and validated by measurements [6]. These die manufacturers have used the level 1 Si Model (STM), the EKV model (ROHM and CREE Wolfspeed ) and the Curtice model (CREE Wolfspeed) for their devices, even though the level 1 Si model and EKV model do not properly adapt to SiC devices. The Curtice model gives a better accuracy and adaptation for these devices. Since its creation which was initially used for GaAs FET [8], consequential works have been completed to adapt this model to MOSFETs. An improved modeling based on Curtice model for SiC MOSFET is proposed [7].

Taking a step back, the idea behind Curtice model is that the hyperbolic tangent function has the same form as the output characteristics of MOSFET. Using this function, we can easily represent output characteristics of SiC MOSFET with a good accuracy by adjusting fewer parameters in the MOSFET equations.

It is natural to think about other functions having the same form and to extend the model by using these functions. The idea here is to see if we can minimize the number of parameters and so decrease the complexity of the model while maintaining the same level of accuracy.

In this particular work, we build our model using the following function instead of the hyperbolic tangent function:

$$f_d(x) = \frac{x}{|x|+b} \quad (1)$$

This function is relatively simple comparing to the hyperbolic tangent function.

## II. SiC MOSFET MODELING

### A. State of the art of Curtice model for SiC MOSFET

In this section, we will present our model of SiC MOSFET. The original Curtice model of MOSFET channel is the following [9]:

$$I_{DS} = f_g(V_{GS}) \times f_d(V_{DS}) \quad (2)$$

where:

$$f_g(V_{GS}) = A_0 + A_1 V_{GS} + A_2 V_{GS}^2 + A_3 V_{GS}^3 \quad (3)$$

$$f_d(V_{DS}) = \tanh(\gamma V_{DS}) (1 + \lambda V_{DS}) \quad (4)$$

The function  $f_g(V_{GS})$  represents transfer characteristics while the function  $f_d(V_{DS})$  represents output characteristics of MOSFET. Some modifications have been realized in order to adapt the model to SiC MOSFET [6].

The function of  $f_g$  has been changed from a cubic polynomial to an algebraic fraction [7]. The idea behind this change is that the new function  $f_g$  suits better the transfer characteristics of SiC MOSFET.

The function  $f_d$ , on the other hand, has been the same hyperbolic tangent function as the Curtice model's one.

### B. New model for SiC MOSFET

Firstly, we separate the MOSFET equation by blocks and normalize the two functions that represent transfer characteristics and output characteristics. The MOSFET equation will have the following formula:

$$I_{DS} = C \times f_g(V_{GS}) \times f_d(V_{DS}) \times (1 + \lambda V_{DS}) \quad (5)$$

where:

$C$  is a constant which relates to the saturation current of SiC MOSFET.

The function:

$$f_g(V_{GS}) = \left( \frac{V_{GS}^n}{V_{GS}^n + a^n} \right)^m \quad (6)$$

is a function  $V_{GS}$ , with coefficients  $a, n, m$ .

The function:

$$f_d(V_{DS}) = \frac{V_{DS}}{|V_{DS}| + b} \quad (7)$$

is a function of  $V_{DS}$ , with coefficient  $b$ .

The factor  $1 + \lambda V_{DS}$  is the modulation factor with  $\lambda$  is channel-length modulation parameter. This factor allows the  $I_{DS}$  compensate the small augmentation of drain current when  $V_{DS}$  becomes very large (in saturation mode).

#### Analysis of the model:

In the function  $f_g(V_{GS})$ , comparing to the function in [7], we replaced the exponential function  $\exp()$  by the power function of  $a$ . The added coefficient  $a$  allows having a better dynamic while fitting the model with measurement. By adjusting the values of  $a, n$  and  $m$ , we can have a different threshold voltage and different curves of the function  $f_g$ . The curve of  $f_g(V_{GS})$  with different sets of parameters  $(a, n, m)$  is illustrated in figure 1.

The function  $f_d(V_{DS})$  has the same curve as the hyperbolic tangent function in the Curtice model. The figure 2 shows several forms of the function  $f_d(V_{DS})$  with different values of  $b$ .

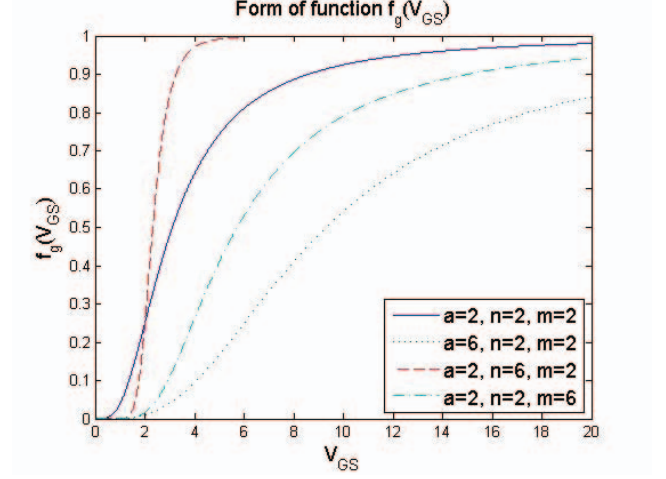


Fig. 1. Curves of the function  $f_g(V_{GS})$ , with different set values of coefficients  $(a, n, m)$ .

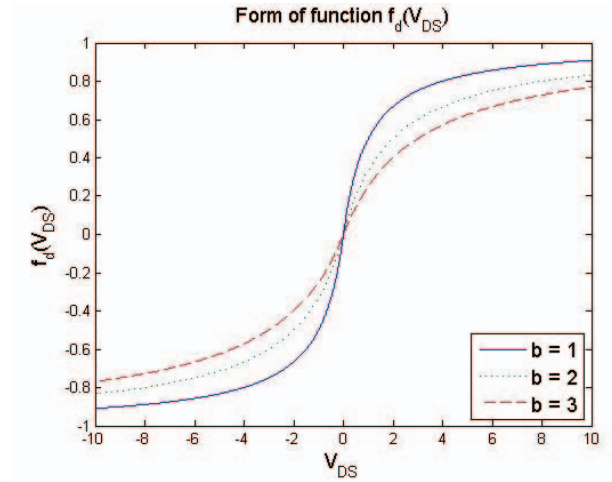


Fig. 2. Curves of the function  $f_d(V_{DS})$  with different values of  $b$ .

The value of  $f_d(V_{DS})$  tends to 1 when  $V_{DS}$  becomes very large. The smaller  $b$  is, the faster  $f_d(V_{DS})$  approaches its asymptote.

In order to have a complete MOSFET equation, we need to find totally 6 mentioned coefficients:  $C, a, n, m, b, \lambda$ .

The conventional procedure is to acquire the output characteristics of devices by experimental measurement. Afterwards, using curve fitting techniques, we will be able to find a set of coefficients that minimize the difference between the simulation curve and the measurement one (method of Least-Squares). The found coefficients will be then employed in the model to plot the simulation curve. A comparison between the simulation curve and measurement will be made in order to evaluate the accuracy of the model.

### III. SIMULATION AND MEASUREMENT

In this third section, in order to validate the accuracy of the built model, we will make use of this model on different SiC MOSFETs from different manufacturers. Two selected SiC MOSFETs are: SCT50N120 (from STM) and SCT2280KE (from ROHM).

Forward output characteristics of these devices are measured by using the curve tracer HP4142b. Here, the drain-source voltage  $V_{DS}$  was measured under different values of the gate-source voltage  $V_{GS}$  (from 12V to 20V) when the drain current  $I_{DS}$  varies from:

- 0 to 10A for forward conduction.
- 0 to -10A for reverse conduction.

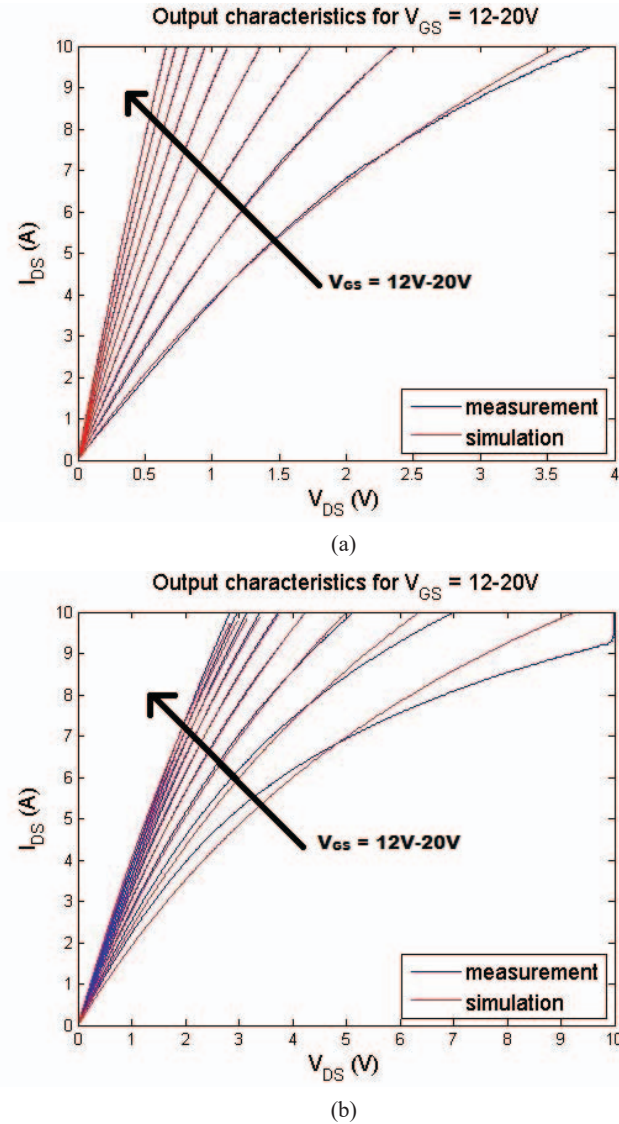


Fig. 3. SiC MOSFET forward output characteristics: simulation vs measurement (a) SCT50N120, (b) SCT2280KE.

In fig. 3, the comparison between simulation and measurement forward output characteristics of these SiC MOSFETs is illustrated.

As we can see in fig. 3, the model gives a pretty good accuracy of forward characteristics at high gate-source voltage  $V_{GS}$  for both devices. While it still maintains a good precision at low gate source voltage  $V_{GS}$  for STM device, its precision decreased for ROHM device under these conditions ( $V_{GS} = 12-13V$ ).

Fig. 4 shows the simulation and measurement comparison for reverse output characteristics ( $I_{SD}$  as function of  $V_{SD}$ ). The model shows a promising accuracy for ROHM device. However, it only give a good precision for STM device under high gate-source voltage  $V_{GS}$ . In the case of low gate-source voltage ( $V_{GS} = 12V$ ), the model still needs to be improved.

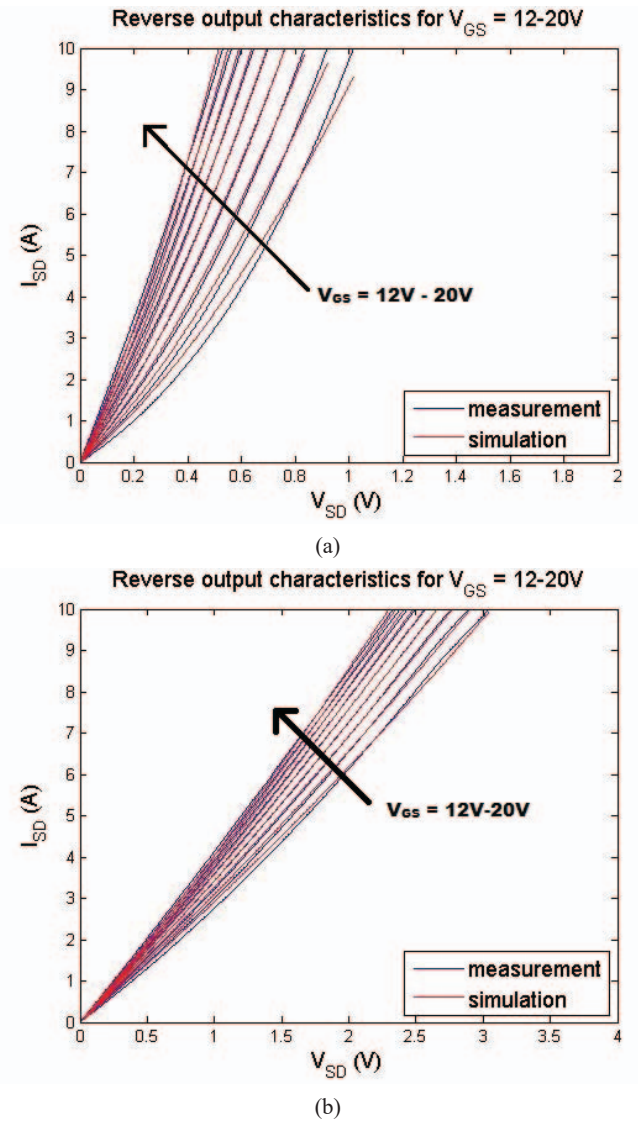


Fig. 4. SiC MOSFET reverse output characteristics: simulation vs measurement (a) SCT50N120, (b) SCT2280KE.

#### IV. CONCLUSION

This paper presents a behavioral electrical model of SiC MOSFETs. Following the funding idea of Curtice model, a different function is used instead of the hyperbolic tangent function in order to represent the output characteristics of MOSFETs.

As illustrated in figure 3, the model showed a promising modeling accuracy vs. measurement. However, the model still needs to be improved to better address static output characteristics at medium gate-source voltage. This might be improved through a better curve fitting strategy in the future.

The model only uses 6 parameters for the functionality of MOSFET channels. For comparison, another model [7], which was also built on the Curtice model, has 12 parameters. However, this model already takes into consideration the variations of characteristics with the junction temperature.

Therefore, taking into account the influence of the junction temperature in our model is a first development to follow.

Secondly, this work should be extended to a fully completed model of SiC MOSFET with dynamic characteristics, body diode characteristics and other aspects.

#### REFERENCES

- [1] M. Bhatnagar; B.J. Baliga, "Comparison of 6H-SiC, 3C-SiC and Si for power devices", IEEE Transactions on Electron Devices (Volume: 40, Issue: 3, Mar 1993).
- [2] Glaser, J. S., Nasadoski, J. J., Losee, P. A., Kashyap, A. S., Matocha, K. S., Garrett, J. L., & Stevanovic, L. D. (2011, March). Direct comparison of silicon and silicon carbide power transistors in high-frequency hard-switched applications. In 2011 Twenty-Sixth Annual IEEE Applied Power Electronics Conference and Exposition (APEC) (pp. 1049-1056). IEEE.
- [3] She, X., Huang, A. Q., Lucia, O., & Ozpineci, B. (2017). Review of silicon carbide power devices and their applications. IEEE Transactions on Industrial Electronics, 64(10), 8193-8205.
- [4] Mantooth, H. A., Peng, K., Santi, E., & Hudgins, J. L. (2015). Modeling of wide bandgap power semiconductor devices—Part I. IEEE Transactions on Electron Devices, 62(2), 423-433.
- [5] McNutt, T. R., Hefner, A. R., Mantooth, H. A., Berning, D., & Ryu, S. H. (2007). Silicon carbide power MOSFET model and parameter extraction sequence. IEEE Transactions on Power Electronics, 22(2), 353-363.
- [6] Stefanskyi, A., Starzak, L., & Napieralski, A. (2017, June). Review of commercial SiC MOSFET models: Validity and accuracy. In 2017 MIXDES-24th International Conference "Mixed Design of Integrated Circuits and Systems (pp. 488-493). IEEE.
- [7] Stefanskyi, A., Starzak, L., & Napieralski, A. (2018, June). Universal Behavioural Model for SiC Power MOSFETs Under Forward Bias. In 2018 25th International Conference "Mixed Design of Integrated Circuits and System"(MIXDES) (pp. 343-348). IEEE.
- [8] Curtice, W. R., & Ettenberg, M. (1985). A nonlinear GaAs FET model for use in the design of output circuits for power amplifiers. IEEE Transactions on Microwave Theory and Techniques, 33(12), 1383-1394.
- [9] S. Maas, "Fixing the Curtice model," Microwave J., 2002.